



# 2N7002KCT

## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

- $V_{DS}$  60V
- $I_D$  0.3A
- $R_{DS(ON)}$  (at  $V_{GS}=10V$ )  $< 2.5\Omega$
- $R_{DS(ON)}$  (at  $V_{GS}=4.5V$ )  $< 3\Omega$
- Gate-Source ESD Rating Up to 2KV (HBM)

### General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	60	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25$	$I_D$	0.3	A
	$T_A=100$		0.2	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	0.9	A
Total Power Dissipation <sup>B</sup>	$T_A=25$	$P_D$	0.34	W
	$T_A=100$		0.13	





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## ■ Electrical Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$	-	-	1	$\mu A$
		$V_{DS}=60V, V_{GS}=0V, T_J=150$	-	-	100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=0.3A$	-	1.8	2.5	$\Omega$
		$V_{GS}=4.5V, I_D=0.2A$	-	2.0	3.0	
Diode Forward Voltage	$V_{SD}$	$I_S=0.3A, V_{GS}=0V$	-	0.9	1.2	V
Gate resistance	$R_G$	$f=1\text{MHz}$ , Open drain	-	130	-	$\Omega$
Maximum Body-Diode Continuous Current	$I_S$		-	-	0.3	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=30V, V_{GS}=0V, f=1\text{MHz}$	-	13	-	$pF$
Output Capacitance	$C_{oss}$		-	5	-	
Reverse Transfer Capacitance	$C_{rss}$		-	1	-	
<b>Switching Parameters</b>						
Total Gate Charge	$Q_g$	$V_{GS}=10V, V_{DS}=30V, I_D=0.3A$	-	1.22	-	$nC$
Gate-Source Charge	$Q_{gs}$		-	0.5	-	
Gate-Drain Charge	$Q_{gd}$		-	0.18	-	
Reverse Recovery Charge	$Q_{rr}$	$I_F=0.3A, di/dt=100A/\mu s$	-	3.6	-	$nC$
Reverse Recovery Time	$t_{rr}$		-	16	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=30V, I_D=0.3A$ $R_{GEN}=50\Omega$	-	7	-	$ns$
Turn-on Rise Time	$t_r$		-	19	-	
Turn-off Delay Time	$t_{D(off)}$		-	20	-	
Turn-off fall Time	$t_f$		-	84	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B.  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.

C. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with  $T_A=25$ . The maximum allowed junction temperature of 150. The value in any given application depends on the user's specific board design.





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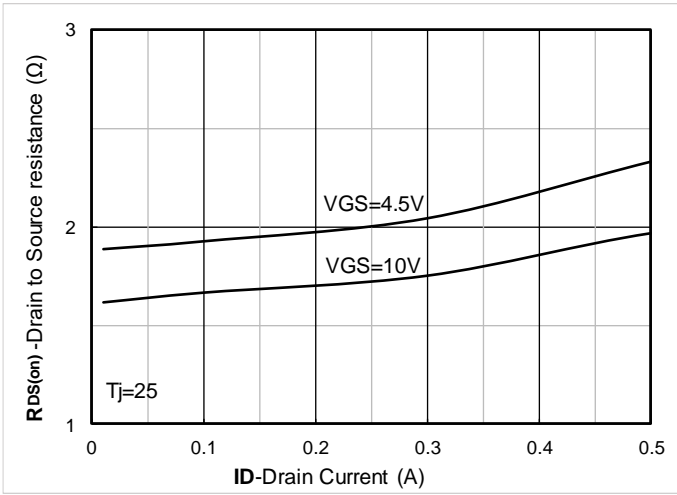


Figure 7. RDS(on) VS Drain Current

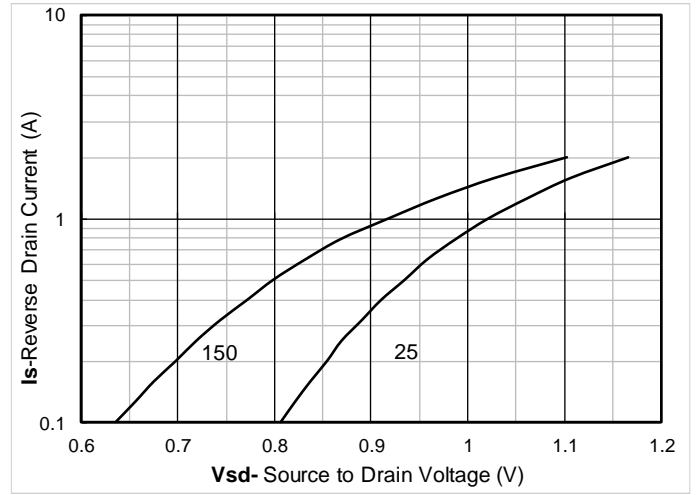


Figure 8. Forward characteristics of reverse diode

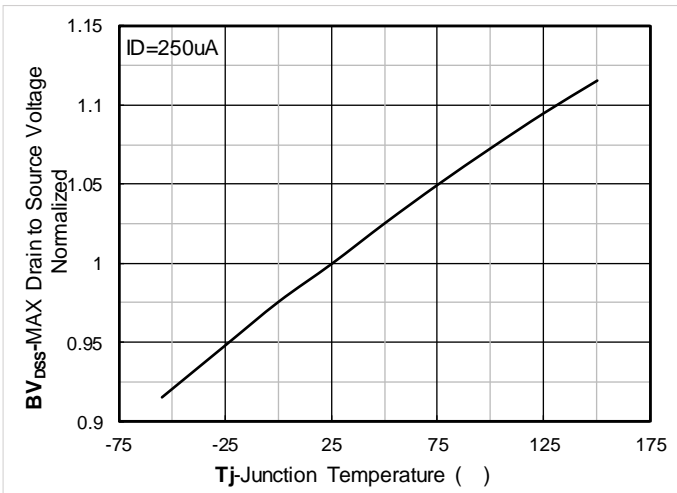


Figure 9. Normalized breakdown voltage

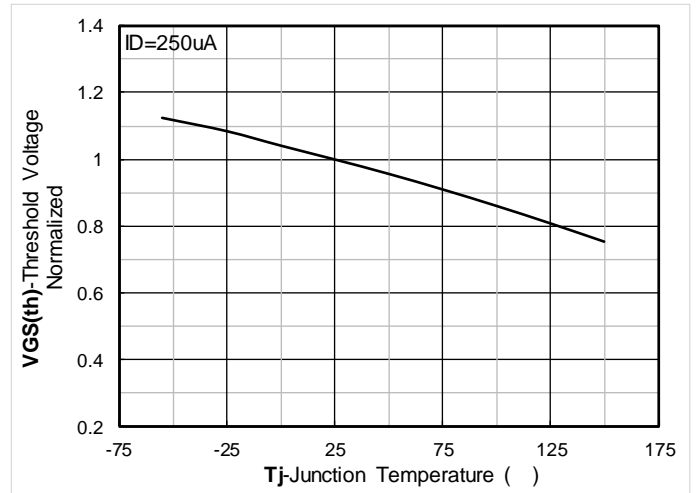


Figure 10. Normalized Threshold voltage

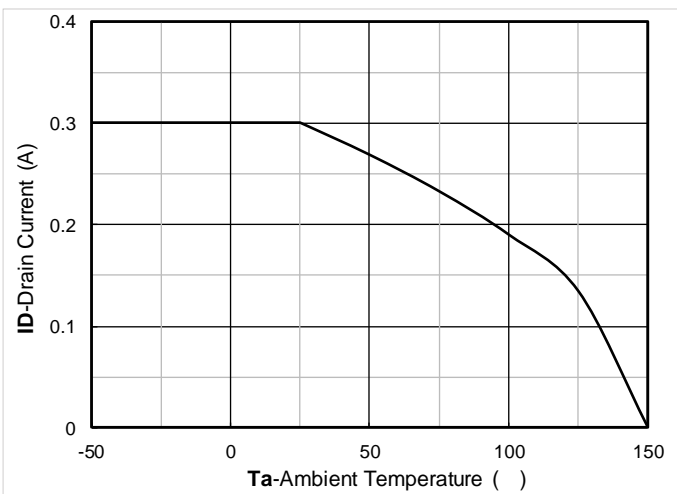


Figure 11. Current dissipation

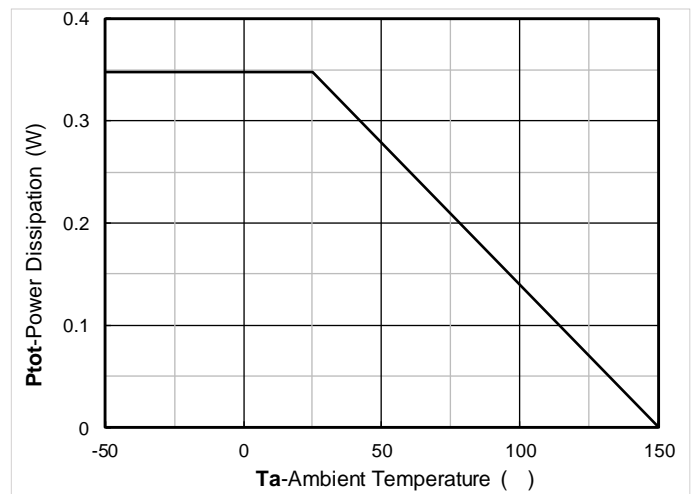


Figure 12. Power dissipation

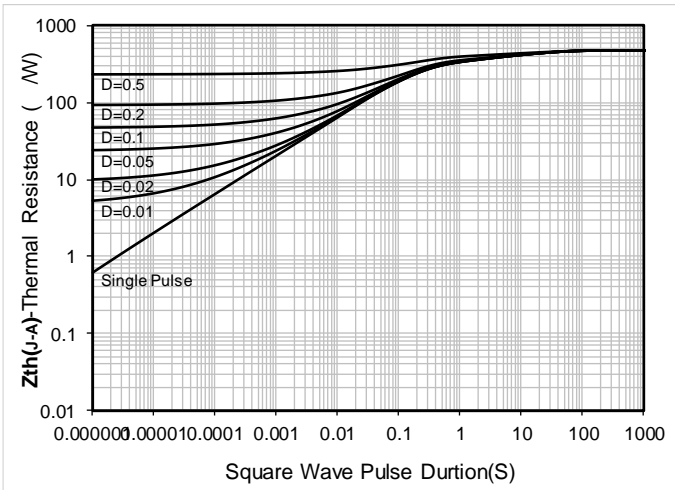


Figure 13. Maximum Transient Thermal Impedance

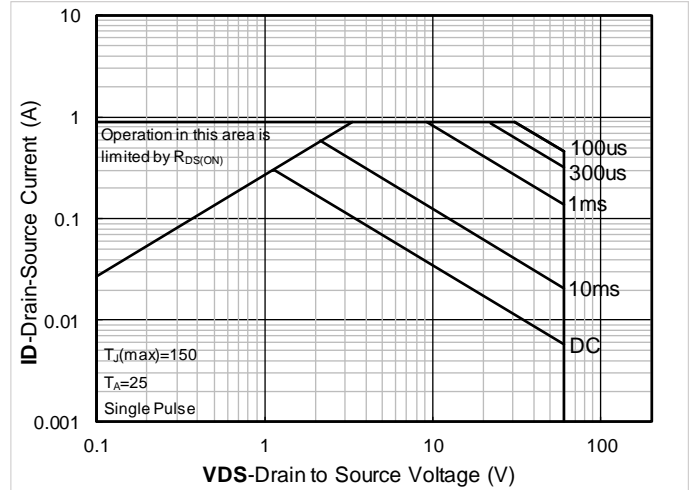


Figure 14. Safe Operation Area

## ■ Test Circuits & Waveforms

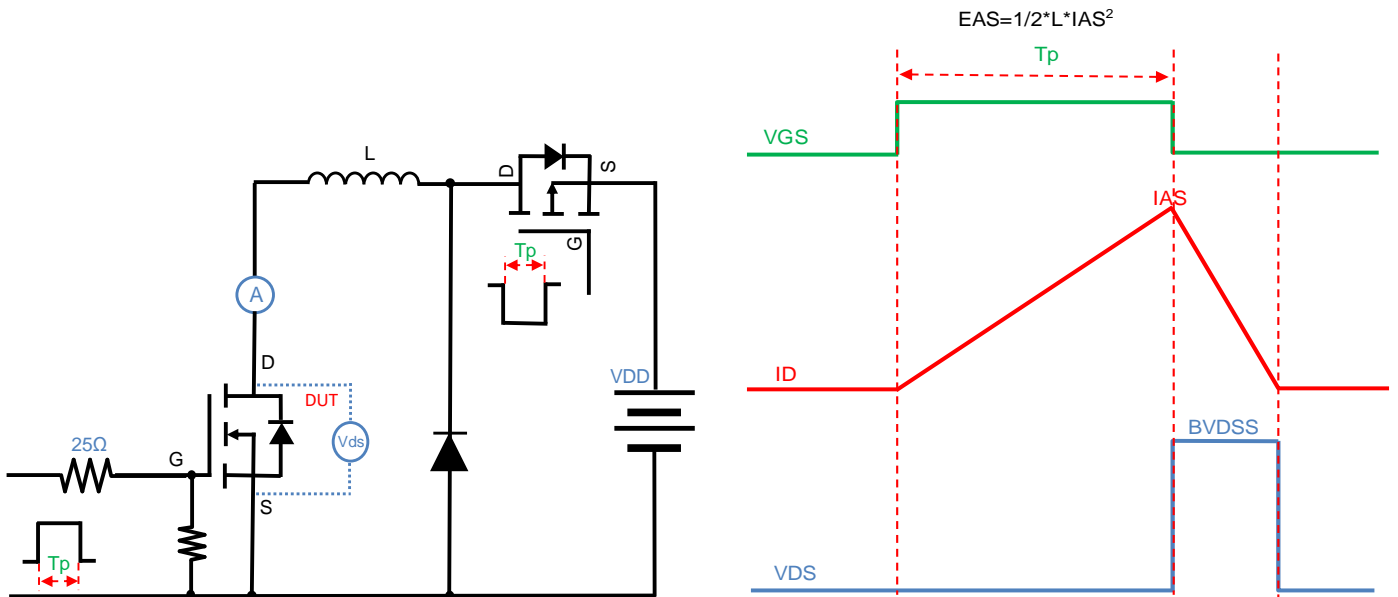


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

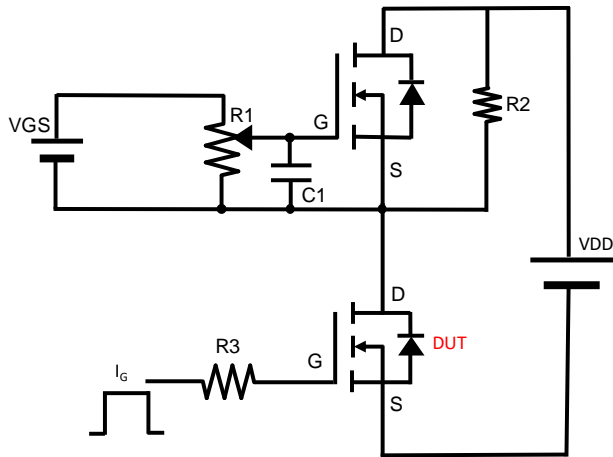


Figure B. Gate Charge Test Circuit & Waveform

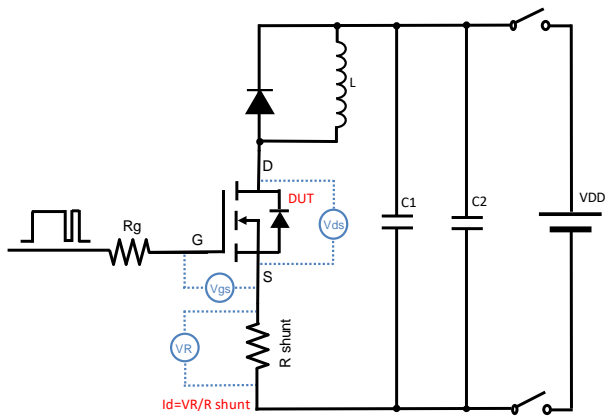


Figure C. Resistive Switching Test Circuit & Waveform

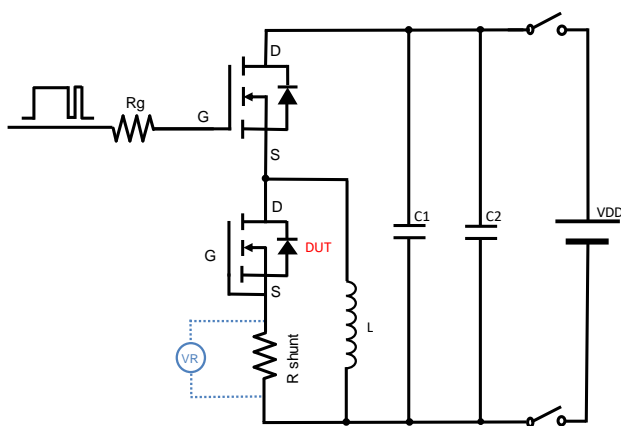
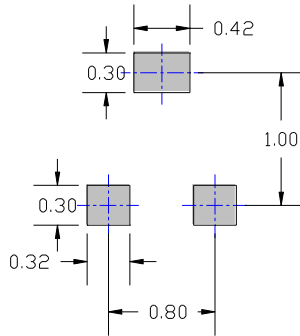
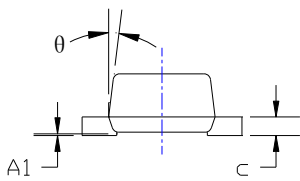
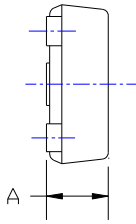
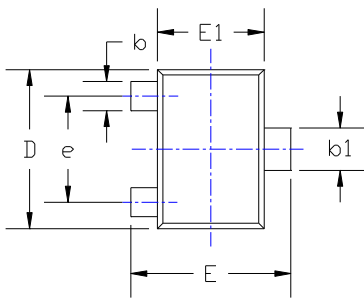


Figure D. Diode Recovery Test Circuit & Waveform

## ■ SOT-723 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.017	0.022	0.430	0.550
A1	0.000	0.002	0.000	0.050
b	0.007	0.011	0.170	0.270
b1	0.011	0.015	0.270	0.370
c	0.003	0.008	0.080	0.200
D	0.045	0.049	1.150	1.250
E	0.045	0.049	1.150	1.250
E1	0.030	0.033	0.750	0.850
e	0.031TYP.		0.800TYP.	
θ	7°REF.		7°REF.	

NOTE:  
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.  
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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